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XPX3N1U9RD

30V N-Channel Enhancement Mode Power MOSFET

## Description

The XPX3N1U9RD uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

### **General Features**

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

## Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



V DS =30V,ID =120A RDS(ON)=1.9mΩ (typ) @ VGS=10V RDS(ON)=2.2mΩ (typ) @ VGS=4.5V





### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
XPX3N1U9RD	XPX3N1U9RD	DFN5X6-8L	-	-	-

### Absolute Maximum Ratings (T<sub>c</sub>=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	30	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι <sub>D</sub>	120	А
Drain Current-Continuous(T <sub>C</sub> =100℃)	I <sub>D</sub> (100℃)	85	A
Pulsed Drain Current	I <sub>DM</sub>	420	A
Maximum Power Dissipation	PD	75	W
Derating factor		0.65	<b>W</b> /°C
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 To 150	°C
Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>θJC</sub>	1.87	°C/W



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## Electrical Characteristics (T<sub>c</sub>=25<sup>°</sup>Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics			•		L	•	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	30	35	-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V	-	-	1	μA	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA	
On Characteristics (Note 3)				•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	0.7	1.1	1.7	V	
Drain Course On State Desistance		V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	1.9	2.2		
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A		2.2	2.9	mΩ	
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =10V,I <sub>D</sub> =20A	35	-	-	S	
Dynamic Characteristics (Note4)				•			
Input Capacitance	C <sub>lss</sub>		-	6869	-	PF	
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V, F=1.0MHz	-	974	-	PF	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	740	-	PF	
Switching Characteristics (Note 4)				•			
Turn-on Delay Time	t <sub>d(on)</sub>		-	25	-	nS	
Turn-on Rise Time	tr	$V_{DD}$ =15V, R <sub>L</sub> =15 $\Omega$	-	26	-	nS	
Turn-Off Delay Time	t <sub>d(off)</sub>	V <sub>GS</sub> =10V,R <sub>G</sub> =2.5Ω	-	98	-	nS	
Turn-Off Fall Time	t <sub>f</sub>		-	40	-	nS	
Total Gate Charge	Qg	N/ 451/1 00A	-	142		nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}=15V,I_{D}=20A,$	-	21		nC	
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	33		nC	
Drain-Source Diode Characteristics			•		L		
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =20A	-		1.2	V	
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	110	А	
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF = 20A	-	20	-	nS	
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	55	-	nC	
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)					

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production



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# **Typical Electrical and Thermal Characteristics (Curves)**





10.0

1.0

0.1

0.0

0.01

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10ms

100

DC

10

1111

1

Vds Drain-Source Voltage (V)

**Figure 8 Safe Operation Area** 

T<sub>J(Max)</sub>=150°C T<sub>C</sub>=25°C

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Figure 9 BV<sub>DSS</sub> vs Junction Temperature



Figure 10 V<sub>GS(th)</sub> vs Junction Temperature







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# DFN5X6-8L Package Information



Sumbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	0.900	1.000	0.035	0.039	
A3	0.254REF.		0.010	REF.	
D	4.944	5.096	0.195	0.201	
E	5.974	6.126	0.235	0.241	
D1	3.910	4.110	0.154	0.162	
E1	3.375	3.575	0.133	0.141	
D2	4.824	4.976	0.190	0.196	
E2	5.674	5.826	0.223	0.229	
k	1.190	1.390	0.047	0.055	
b	0.350	0.450	0.014	0.018	
e	1.270TYP.		0.050TYP.		
L	0.559	0.711	0.022	0.028	
L1	0.424	0.576	0.017	0.023	
Н	0.574	0.726	0.023	0.029	
θ	8°	12°	8°	12°	



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#### Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time	
Pb device	<b>245℃±5</b> ℃	5sec±1sec	
Pb-Free device	<b>260℃+0/-5℃</b>	5sec±1sec	



This integrated circuit can be damaged by ESD UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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